

#5/A  
7/19/07

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re PATENT APPLICATION OF

Inventor(s): ITO et al.

Filed: Herewith

Title: GROUP III NITRIDE COMPOUND SEMICONDUCTOR DEVICE

December 18, 2001

PRELIMINARY AMENDMENT

Hon. Commissioner of Patents  
Washington, D.C. 20231

Sir:

Please amend this application as follows:

IN THE SPECIFICATION:

At the top of the first page, just under the title, insert:

A1 This is a Divisional of U.S. Application No. 09/518,724, filed March 3, 2000,  
the entire contents of which are incorporated by reference.

Please amend the specification as follows:

Page 1, delete the whole paragraph starting with line 5 and replace it with the  
following new paragraph.

A2 This invention relates to a group III nitride compound semiconductor device. More  
particularly, it relates to an improvement in an undercoat layer for a group III nitride  
compound semiconductor layer such as a GaN semiconductor layer.